



2N7002T

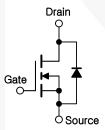
N-Channel Enhancement Mode Field Effect Transistor

Features

- · Low On-Resistance
- · Low Gate Threshold Voltage
- · Low Input Capacitance
- · Fast Switching Speed
- · Low Input/Output Leakage
- · Ultra-Small Surface Mount Package
- · Lead Free/RoHS Compliant



SOT - 523F



Ordering Information

Part Number	Number Top Mark Package		Packing Method	
2N7002T	AA SOT-523F 3L		Tape and Reel	

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter		Value	Unit
V _{DSS}	Drain-Source Voltage		60	V
V_{DGR}	Drain-Gate Voltage (R _{GS} ≤ 1.0 MΩ)		60	V
V _{GSS} Gate-Source Voltage	Cata Sauras Valtaga	Continuous	±20	V
	Gale-Source voltage	Pulsed	±40	
	Continuous	Continuous	115	mA
I _D	Drain Current	Continuous at 100°C	73	
		Pulsed	800	
TJ	Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to +150	°C

© 2079 Fairchild Semiconductor Corporation 2N7002T Rev. 1.1

Thermal Characteristics

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Value	Unit
Total Device Dissipation		200	mW
P _D	Derate Above T _A = 25°C	1.6	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient ⁽¹⁾	625	°C/W

Note:

1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch. Minimum land pad size.

Electrical Characteristics

Values are at T_A = 25°C unless otherwise noted.

Parameter	Conditions	Min.	Тур.	Max.	Unit
eristics ⁽²⁾					
Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 10 \mu\text{A}$	60	78		V
	V _{DS} = 60 V, V _{GS} = 0 V		0.001	1.0	μΑ
Zero Gate Voltage Drain Current	V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125°C		7	500	
Gate-Body Leakage	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$		0.2	±10	nA
eristics ⁽²⁾		•			
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1.00	1.76	2.00	V
	$V_{GS} = 5 \text{ V}, I_D = 0.05 \text{ A}$		1.6	7.5	Ω
Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 0.5 A			2.0	
otatio Brain Godree On Resistance	V _{GS} = 10 V, I _D = 0.5 A, T _J = 125°C		2.53	13.5	
On-State Drain Current	V _{GS} = 10 V, V _{DS} = 7.5 V	0.50	1.43		Α
Forward Transconductance	V _{DS} = 10 V, I _D = 0.2 A	80.0	356.5		mS
naracteristics		•			
Input Capacitance	.,		37.8	50	pF
Output Capacitance			12.4	25	pF
Reverse Transfer Capacitance	1.0 Will 12		6.5	7	pF
Characteristics					
Turn-On Delay Time			20	ns	
Turn-Off Delay Time	V_{GEN} = 10 V, R _L = 150 Ω , R _{GEN} = 25 Ω		12.5	20	ns
	Prain-Source Breakdown Voltage Zero Gate Voltage Drain Current Gate-Body Leakage Pristics ⁽²⁾ Gate Threshold Voltage Static Drain-Source On-Resistance On-State Drain Current Forward Transconductance Practeristics Input Capacitance Output Capacitance Reverse Transfer Capacitance Characteristics Turn-On Delay Time	eristics(2)Drain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}, I_D = 10 \text{ μA}$ Zero Gate Voltage Drain Current $V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 60 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Body Leakage $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ eristics(2) $V_{DS} = V_{GS}, I_D = 250 \text{ μA}$ Gate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250 \text{ μA}$ $V_{GS} = 5 \text{ V}, I_D = 0.05 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 0.5 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 0.5 \text{ A}$ $V_{DS} = 10 \text{ V}, I_D = 0.5 \text{ A}$ Forward Transconductance $V_{DS} = 10 \text{ V}, I_D = 0.2 \text{ A}$ ParacteristicsInput Capacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ Ontput Capacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ Paracteristics $V_{DS} = 30 \text{ V}, I_D = 0.2 \text{ A},$ Turn-On Delay Time $V_{DD} = 30 \text{ V}, I_D = 0.2 \text{ A},$ $V_{GEN} = 10 \text{ V}, R_L = 150 \Omega,$	eristics ⁽²⁾ Drain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}$, $I_D = 10 \text{ μA}$ 60 VDS = 60 V, VGS = 0 V $V_{DS} = 60 \text{ V}$, $V_{GS} = 0 \text{ V}$ VDS = 60 V, $V_{GS} = 0 \text{ V}$ $V_{DS} = 60 \text{ V}$, $V_{DS} = 0 \text{ V}$ Gate-Body Leakage $V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$ Peristics ⁽²⁾ $V_{DS} = V_{GS}$, $I_D = 250 \text{ μA}$ 1.00 Static Drain-Source On-Resistance $V_{DS} = V_{GS}$, $I_D = 0.05 \text{ A}$ $V_{GS} = 10 \text{ V}$, $I_D = 0.5 \text{ A}$ VGS = 10 V, $I_D = 0.5 \text{ A}$ $V_{GS} = 10 \text{ V}$, $V_{DS} = 7.5 \text{ V}$ 0.50 Forward Transconductance $V_{DS} = 10 \text{ V}$, $V_{DS} = 0.2 \text{ A}$ 80.0 Paracteristics $V_{DS} = 25 \text{ V}$, $V_{GS} = 0 $	Pristics (2) Drain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}, I_D = 10 \text{ μA}$ 60 78 Zero Gate Voltage Drain Current $V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$ 0.001 Zero Gate Voltage Drain Current $V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$ 7 Gate-Body Leakage $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ 0.2 Pristics (2) Gate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250 \text{ μA}$ 1.00 1.76 Static Drain-Source On-Resistance $V_{GS} = 10 \text{ V}, I_D = 0.05 \text{ A}$ 1.6 1.6 V _{GS} = 10 V, I _D = 0.5 A, T _J = 125°C 2.53 2.53 On-State Drain Current $V_{GS} = 10 \text{ V}, V_{DS} = 7.5 \text{ V}$ 0.50 1.43 Forward Transconductance $V_{DS} = 10 \text{ V}, I_D = 0.2 \text{ A}$ 80.0 356.5 Paracteristics Input Capacitance 37.8 12.4 Output Capacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, I_D = 0.2 \text{ A}, I_D =$	Peristics (2) Drain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}, I_D = 10 \text{ μA}$ 60 78 Zero Gate Voltage Drain Current $V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$ 0.001 1.0 V _{DS} = 60 V, V _{GS} = 0 V, V _{DS} = 0 V 7 500 Gate-Body Leakage $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ 7 500 eristics(2) V _{DS} = V _{GS} , I _D = 250 μA 1.00 1.76 2.00 Static Drain-Source On-Resistance $V_{GS} = 5 \text{ V}, I_D = 0.05 \text{ A}$ 1.6 7.5 V _{GS} = 10 V, I _D = 0.5 A, T _J = 125°C 2.53 13.5 On-State Drain Current $V_{GS} = 10 \text{ V}, I_D = 0.5 \text{ A}$, T _J = 125°C 2.53 13.5 On-State Drain Current $V_{GS} = 10 \text{ V}, I_D = 0.2 \text{ A}$ 80.0 356.5 Paracteristics Input Capacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz 37.8 50 Output Capacitance $V_{DS} = 30 \text{ V}, I_D = 0.2 \text{ A},$ VGEN = 10 V, R _L = 150 Ω, 5.85 20 Turn-On Delay Time $V_{DD} = 30 \text{ V}, I_D = 0.2 \text{ A},$ VGEN = 10 V, R _L = 150 Ω, 12.4 5.85 20

Note:

2. Short duration test pulse used to minimize self-heating effect.

Typical Performance Characteristics

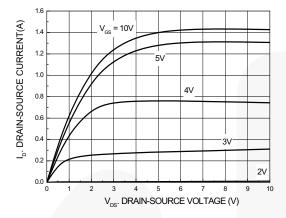


Figure 1. On-Region Characteristics

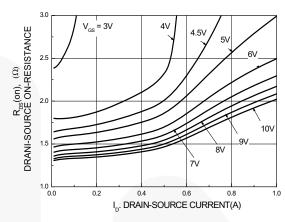


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

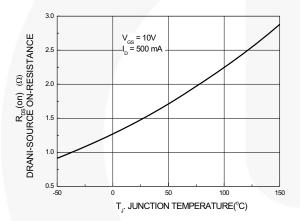


Figure 3. On-Resistance Variation with Temperature

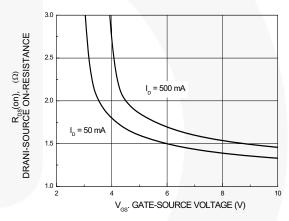


Figure 4. On-Resistance Variation with Gate-Source Voltage

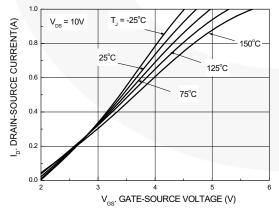


Figure 5. Transfer Characteristics

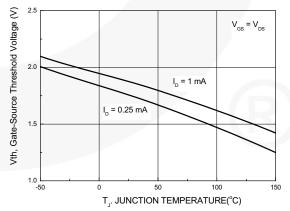


Figure 6. Gate Threshold Variation with Temperature

Typical Performance Characteristics (Continued)

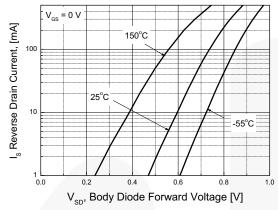


Figure 7. Reverse Drain Current Variation with Diode Forward Voltage and Temperature

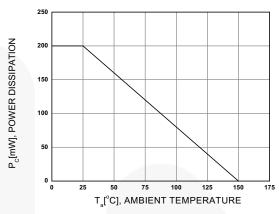
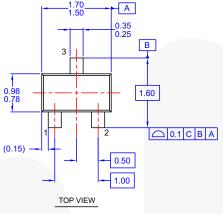
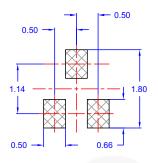


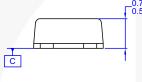
Figure 8. Power Derating

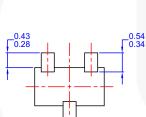
Physical Dimensions



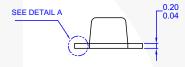


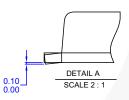
LAND PATTERN RECOMMENDATION





BOTTOM VIEW





- NOTES: A) THIS PACKAGE CONFORMS TO EIAJ SC89 PACKAGING STANDARD.
- B) ALL DIMENSIONS ARE IN MILLIMETERS. C) DRAWING CONFORMS TO ASME Y14.5M-1994
- D) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.

MAD03ArevA

Figure 9. 3-LEAD, SC89, EIAJ-SC89, 0.88MM WIDE, SOT523F





TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

BitSiC™ Green FPS™

Build it Now™ Green FPS™ e-Series™

Current Transfer Logic™ Making Small Speakers Sound Louder DEUXPEED® and Better™

Dual Cool™

EcoSPARK®

EfficientMax™

ESBC™

MicroPak™

MicroPak™

MicroPak™

MicroPak™

Fairchild®
Fairchild Semiconductor®
FACT Quiet Series™
FACT®
FAST®
FastvCore™
FETBench™
FPS™

MillerDrive™
MotionMax™
MotionGrid®
MTT®
MVN®
MVN®
MVN®
MWSaver®
OptoHiT™
OPTOLOGIC®

OPTOPLANAR®

® PowerTrench® PowerXS™

Programmable Active Droop™

QFET[®]
QS™
Quiet Series™
RapidConfigure™

Saving our world, 1mW/W/kW at a time™

SignalWise™ SmartMax™ SMART START™

Solutions for Your Success™

SPM®
STEALTH™
SuperFET®
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SupreMOS®
SyncFET™
Sync-Lock™

SYSTEM GENERAL®

TinyBoost®
TinyBuck®
TinyCalc™
TinyLogic®
TiNYOPTO™
TinyPower™
TinyPWM™
TinyWire™
TranSiC™
TriEquit Detect

TriFault Detect™
TRUECURRENT®*
µSerDes™

Scripes"
UHC®"
Ultra FRFET™
UniFET™
VCX™
VisualMax™
VoltagePlus™
XS™
Msens™
仙童™

* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. TO OBTAIN THE LATEST, MOST UP-TO-DATE DATASHEET AND PRODUCT INFORMATION, VISIT OUR WEBSITE AT http://www.fairchildsemi.com, FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OF CIRCUIT DESCRIBED HEREIN, NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Definition of Terms			
Datasheet Identification	Product Status	Definition	
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.	
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.	
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.	
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.	

Rev. 173

© Fairchild Semiconductor Corporation

www.fairchildsemi.com

ON Semiconductor and III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative